

Title (en)

METHOD AND DEVICES FOR THE APPLICATION OF TRANSPARENT SILICON DIOXIDE LAYERS FROM THE GAS PHASE

Title (de)

VERFAHREN UND VORRICHTUNGEN ZUM AUFBRINGEN VON TRANSPARENTEN SILIZIUMDIOXID-SCHICHTEN AUS DER GASPHASE

Title (fr)

PROCÉDÉ ET DISPOSITIF POUR APPLIQUER DES COUCHES TRANSPARENTES DE DIOXYDE DE SILICIUM EN PHASE GAZEUSE

Publication

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Application

**EP 08715541 A 20080305**

Priority

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Abstract (en)

[origin: WO2008106955A2] The invention relates to a method and to devices for the application of transparent silicon dioxide layers from the gas phase, wherein precursors are introduced into a furnace by means of a carrier gas, characterized in that a liquid phase process is connected upstream of the gas phase process, wherein for the liquid gas phase a process is used that would run as a quasi sol gel process of base chemicals having silicon up to the creation of a silicon dioxide gel, however, the liquid phase process is interrupted during the beginning of the sol phase in that the reaction mixture evaporates with the precursors present, is mixed with the carrier gas, and transported to the furnace.

IPC 8 full level

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Citation (search report)

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